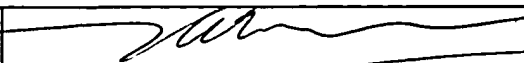


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Examiner Name	Unknown	
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Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES		Sheet 1 of 1

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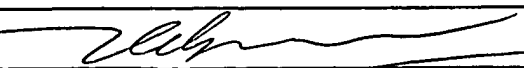


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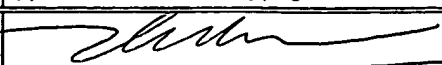
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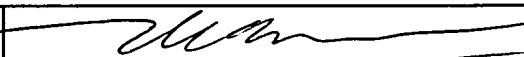
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